

## ABSTRACT OF THE DISCLOSURE

A ferroelectric film wherein 5 to 40 mol% in total of at least one of Nb, V, and W is included in the B site of a Pb(Zr,Ti)O<sub>3</sub> ferroelectric which includes at least 5 four-fold coordinated Si<sup>4+</sup> or Ge<sup>4+</sup> in the A site ion of a ferroelectric perovskite material in an amount of 1% or more. This enables to significantly improve reliability of the ferroelectric film.